

Product data sheet

1. General description

Ultrafast power diode in a SOD142 (2-lead TO247) plastic package.

2. Features and benefits

- · Fast switching and soft reverse recovery characteristics
- Low forward voltage drop
- Low leakage current
- Low reverse recovery current
- Reduces switching losses in associated MOSFET or IGBT

3. Applications

- UPS
- EV Charger
- Welding Machine
- Air Conditioner

4. Quick reference data

Table 1. Quick reference	data	
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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _R	reverse voltage	DC		-	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 129 °C; square-wave pulse; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>		-	-	60	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; T _{j(init)} = 25 °C; sine-wave pulse; Fig. 4		-	-	600	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		-	-	660	A
Static chara	acteristics		•				
V _F	forward voltage	I _F = 60 A; T _j = 25 °C; <u>Fig. 6</u>		-	1.55	2	V
		I _F = 60 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.2	1.6	V
Dynamic ch	naracteristics				·		
t _{rr}	reverse recovery time	I _F = 1 A; V _R = 30 V; dI _F /dt = 50 A/μs; T _j = 25 °C; <u>Fig. 7</u>		-	-	55	ns

5. Pinning information

Table 2. F	Pinning inf	formation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode		K A
2	А	anode		001aaa020
mb	mb	mounting base; connected to cathode	TO-247 (SOD142)	

6. Ordering information

Table 3. Ordering infor	mation				
Type number	Package				
	Name	Description	Version		
BYV60W-600P	TO-247	Plastic Single-ended through-hole package; Heatsink mounted; 1 mounting hole; 2-lead TO-247	SOD142		

BYV60W-600P



7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
V _R	reverse voltage	DC	-	600	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _{mb} ≤ 129 °C; square-wave pulse; <u>Fig. 1; Fig. 2; Fig. 3</u>	-	60	A
I _{FRM}	repetitive peak forward current	δ = 0.5 ; t _p = 25 μs; T _{mb} ≤ 129 °C; square-wave pulse	-	120	A
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	600	A
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4	-	660	A
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-	175	°C

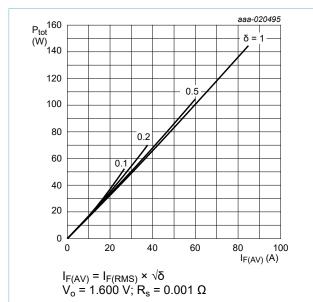
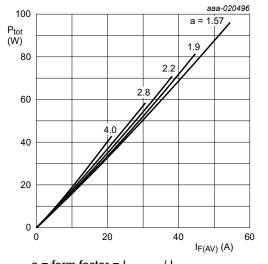


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



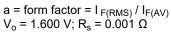
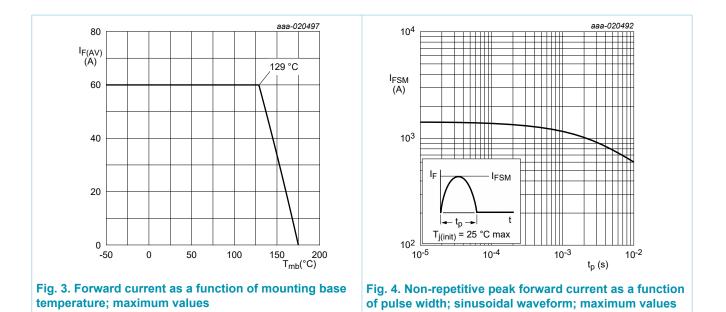


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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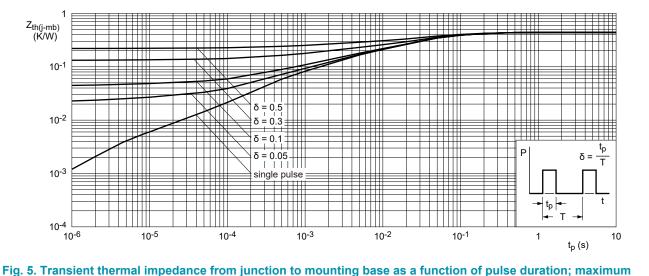


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8. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5	-	-	0.44	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	45	-	K/W

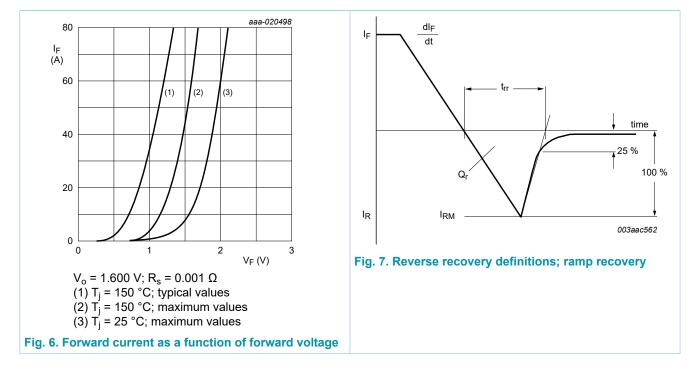


values

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9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _F	forward voltage	I _F = 60 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.55	2	V
		I _F = 60 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.2	1.6	V
R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	10	μA
		V _R = 600 V; T _j = 125 °C	-	-	500	μA
Dynamic ch	naracteristics	· · · · ·				
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 50 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	55	ns
		$I_F = 60 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/ \mu s; T_j = 25 ^{\circ}\text{C}; Fig. 7$	-	53	-	ns
		$I_F = 60 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/ \mu s; T_j = 125 ^{\circ}\text{C}; Fig. 7$	-	120	-	ns
I _{RM}	peak reverse recovery current	$I_F = 60 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/$ µs; $T_j = 25 \text{ °C}; Fig. 7$	-	5.4	-	A
		$I_F = 60 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/$ µs; $T_j = 125 \text{ °C}; Fig. 7$	-	14.5	-	A
Qr	recovered charge	$I_F = 60 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/$ µs; T _j = 25 °C; Fig. 7	-	143	-	nC
		$I_F = 60 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/$ µs; $T_j = 125 \text{ °C}; Fig. 7$	-	876	-	nC
AS	non-repetitive avalanche energy	I _R = 2.2 A; T _{j(init)} = 25 °C; L = 40 mH	-	97	-	mJ



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10. Package outline

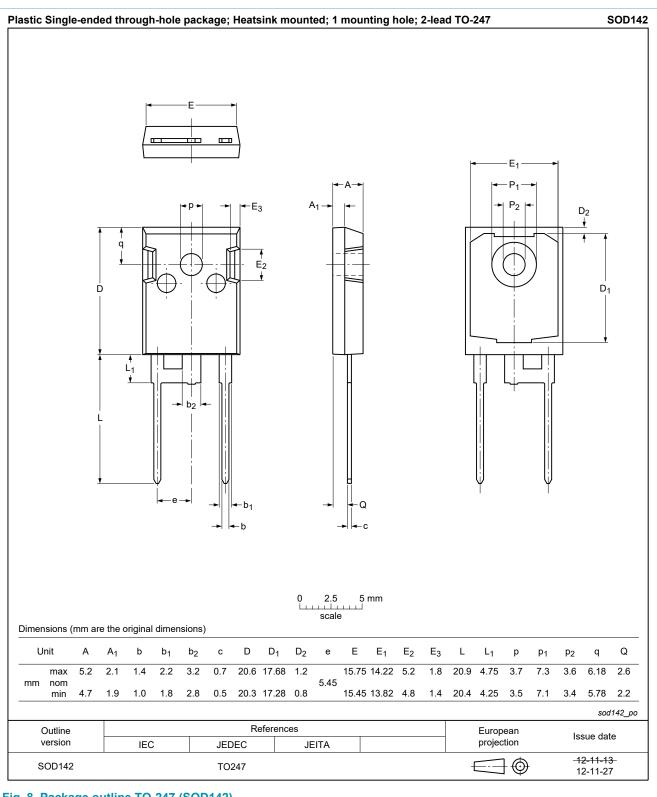


Fig. 8. Package outline TO-247 (SOD142)

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11. Legal information

Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- [2] The term 'short data sheet' is explained in section "Definitions".
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